# RENESAS FemtoClock® Crystal-to-3.3V LVPECL Clock Generator

# **843251-04**

**DATA SHEET**

## **General Description**

The 843251-04 is a 10Gb/12Gb Ethernet Clock Generator. The 843251-04 can synthesize 10 Gigabit Ethernet and 12 Gigabit Ethernet with a 25MHz crystal. It can also generate SATA and 10Gb Fibre Channel reference clock frequencies with the appropriate choice of crystals. The 843251-04 has excellent phase jitter performance and is packaged in a small 8-pin TSSOP, making it ideal for use in systems with limited board space.

## **Features**

- **•** One differential 3.3V LVPECL output
- **•** Crystal oscillator interface designed for 18pF parallel resonant crystal
- **•** Crystal input frequency range: 19.33MHz 30MHz
- **•** Output frequency range: 145MHz 187.5MHz
- **•** VCO range: 580MHz 750MHz
- **•** RMS phase jitter @ 156.25MHz, (1.875MHz 20MHz): 0.39ps (typical)
- **•** Full 3.3V supply mode
- **•** 0°C to 70°C ambient operating temperature
- **•** Available in lead-free (RoHS 6) package



#### **Configuration Table with 25MHz Crystal**

#### **Configuration Table with Selectable Crystals**



## **Block Diagram**



# **Pin Assignment**



**843251-04 8 Lead TSSOP 4.40mm x 3.0mm package body**

## **Pin Description and Pin Characteristic Tables**

**Table 1. Pin Descriptions**



NOTE: Pulldown refers to internal input resistors. See Table 2, Pin Characteristics, for typical values.

#### **Table 2. Pin Characteristics**



# **Absolute Maximum Ratings**

NOTE: Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the *DC Characteristics or AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.



# **DC Electrical Characteristics**

**Table 3A. Power Supply DC Characteristics,**  $V_{CC} = 3.3V \pm 5\%$ ,  $V_{EE} = 0V$ ,  $T_A = 0^{\circ}C$  to 70°C





## **Table 3B. LVCMOS/LVTTL DC Characteristics,**  $V_{CC} = 3.3V \pm 5\%$ **,**  $V_{EE} = 0V$ **,**  $T_A = 0^{\circ}C$  **to 70°C**

#### **Table 3C. LVPECL DC Characteristics,**  $V_{CC} = 3.3V \pm 5\%$ ,  $V_{EE} = 0V$ ,  $T_A = 0^{\circ}C$  to 70°C



NOTE 1: Outputs termination with 50 $\Omega$  to V<sub>CC</sub> – 2V.

#### **Table 4. Crystal Characteristics**



# **AC Electrical Characteristics**

**Table 5. AC Characteristics,**  $V_{CC} = 3.3V \pm 5\%$ ,  $V_{EE} = 0V$ ,  $T_A = 0^{\circ}C$  to 70°C



NOTE: Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lfpm. The device will meet specifications after thermal equilibrium has been reached under these conditions.

NOTE 1: Please refer to Phase Noise Plots.

Noise Power dBc

**Typical Phase Noise at 187.5MHz**



Offset Frequency (Hz)

**Typical Phase Noise at 156.25MHz**

![](_page_4_Figure_2.jpeg)

**Parameter Measurement Information**

![](_page_5_Figure_2.jpeg)

**3.3V LVPECL Output Load AC Test Circuit**

![](_page_5_Figure_4.jpeg)

**Output Duty Cycle/Pulse Width/Period**

![](_page_5_Figure_6.jpeg)

**RMS Phase Jitter**

![](_page_5_Figure_8.jpeg)

![](_page_5_Figure_9.jpeg)

# **Application Information**

## **Power Supply Filtering Technique**

As in any high speed analog circuitry, the power supply pins are vulnerable to random noise. To achieve optimum jitter performance, power supply isolation is required. The 843251-04 provides separate power supplies to isolate any high switching noise from the outputs to the internal PLL.  $V_{CC}$  and  $V_{CCA}$  should be individually connected to the power supply plane through vias, and 0.01µF bypass capacitors should be used for each pin. *Figure 1*  illustrates this for a generic  $V_{CC}$  pin and also shows that  $V_{CCA}$ requires that an additional 10 $\Omega$  resistor along with a 10 $\mu$ F bypass capacitor be connected to the  $V_{CCA}$  pin.

![](_page_6_Figure_4.jpeg)

**Figure 1. Power Supply Filtering**

## **Crystal Input Interface**

The 843251-04 has been characterized with 18pF parallel resonant crystals. The capacitor values, C1 and C2, shown in *Figure 2* below were determined using a 25MHz, 18pF parallel resonant crystal and were chosen to minimize the ppm error. The optimum C1 and C2 values can be slightly adjusted for different board layouts.

![](_page_6_Figure_8.jpeg)

**Figure 2. Crystal Input Interface**

# **Overdriving the XTAL Interface**

The XTAL\_IN input can be overdriven by an LVCMOS driver or by one side of a differential driver through an AC coupling capacitor. The XTAL\_OUT pin can be left floating. The amplitude of the input signal should be between 500mV and 1.8V and the slew rate should not be less than 0.2V/ns. For 3.3V LVCMOS inputs, the amplitude must be reduced from full swing to at least half the swing in order to prevent signal interference with the power rail and to reduce internal noise. *Figure 3A* shows an example of the interface diagram for a high speed 3.3V LVCMOS driver. This configuration requires that the sum of the output impedance of the driver (Ro) and the series resistance (Rs) equals the transmission line impedance. In addition, matched termination at the crystal input will attenuate the signal in half. This can be done in one of two

ways. First, R1 and R2 in parallel should equal the transmission line impedance. For most  $50\Omega$  applications, R1 and R2 can be 100 $\Omega$ . This can also be accomplished by removing R1 and changing R2 to 50 $\Omega$ . The values of the resistors can be increased to reduce the loading for a slower and weaker LVCMOS driver. *Figure 3B* shows an example of the interface diagram for an LVPECL driver. This is a standard LVPECL termination with one side of the driver feeding the XTAL\_IN input. It is recommended that all components in the schematics be placed in the layout. Though some components might not be used, they can be utilized for debugging purposes. The datasheet specifications are characterized and guaranteed by using a quartz crystal as the input.

![](_page_7_Figure_4.jpeg)

**Figure 3A. General Diagram for LVCMOS Driver to XTAL Input Interface**

![](_page_7_Figure_6.jpeg)

**Figure 3B. General Diagram for LVPECL Driver to XTAL Input Interface**

## **Termination for 3.3V LVPECL Outputs**

The clock layout topology shown below is a typical termination for LVPECL outputs. The two different layouts mentioned are recommended only as guidelines.

The differential outputs are low impedance follower outputs that generate ECL/LVPECL compatible outputs. Therefore, terminating resistors (DC current path to ground) or current sources must be used for functionality. These outputs are designed to drive  $50\Omega$ 

![](_page_8_Figure_4.jpeg)

**Figure 4A. 3.3V LVPECL Output Termination Figure 4B. 3.3V LVPECL Output Termination**

transmission lines. Matched impedance techniques should be used to maximize operating frequency and minimize signal distortion. *Figures 4A and 4B* show two different layouts which are recommended only as guidelines. Other suitable clock layouts may exist and it would be recommended that the board designers simulate to guarantee compatibility across all printed circuit and clock component process variations.

![](_page_8_Figure_7.jpeg)

### **Schematic Example**

*Figure 5* shows an example of 843251-04 application schematic. In this example, the device is operated at  $V_{CC} = 3.3V$ . The 18pF parallel resonant 25MHz crystal is used. The C1 = 33pF and C2 = 27pF are recommended for frequency accuracy. For different

board layout, the C1 and C2 may be slightly adjusted for optimizing frequency accuracy. Two examples of LVPECL termination are shown in this schematic. Additional termination approaches are shown in the *LVPECL Termination Application Note.*

![](_page_9_Figure_4.jpeg)

**Figure 5. 843251-04 Schematic Example**

# **Power Considerations**

This section provides information on power dissipation and junction temperature for the 843251-04. Equations and example calculations are also provided.

#### **1. Power Dissipation.**

The total power dissipation for the 843251-04 is the sum of the core power plus the power dissipated in the load(s). The following is the power dissipation for  $V_{CC} = 3.3V + 5\% = 3.465V$ , which gives worst case results.

NOTE: Please refer to Section 3 for details on calculating power dissipated in the load.

- Power (core)<sub>MAX</sub> =  $V_{CC}$  <sub>MAX</sub> \* I<sub>EE\_MAX</sub> = 3.465V \* 70mA = **242.55mW**
- Power (outputs)<sub>MAX</sub> = 30mW/Loaded Output pair

**Total Power**<sub> $-MAX$ </sub> (3.3V, with all outputs switching) = 242.55mW + 30mW = 272.55mW

#### **2. Junction Temperature.**

Junction temperature, Tj, is the temperature at the junction of the bond wire and bond pad directly affects the reliability of the device. The maximum recommended junction temperature is 125°C. Limiting the internal transistor junction temperature, Tj, to 125°C ensures that the bond wire and bond pad temperature remains below 125°C.

The equation for Tj is as follows: Tj =  $\theta_{JA}$  \* Pd\_total + T<sub>A</sub>

Tj = Junction Temperature

 $\theta_{JA}$  = Junction-to-Ambient Thermal Resistance

Pd\_total = Total Device Power Dissipation (example calculation is in section 1 above)

 $T_A$  = Ambient Temperature

In order to calculate junction temperature, the appropriate junction-to-ambient thermal resistance  $\theta_{JA}$  must be used. Assuming no air flow and a multi-layer board, the appropriate value is 129.5°C/W per Table 6 below.

Therefore, Tj for an ambient temperature of 70°C with all outputs switching is:

 $70^{\circ}$ C + 0.273W  $*$  129.5°C/W = 105.4°C. This is well below the limit of 125°C.

This calculation is only an example. Tj will obviously vary depending on the number of loaded outputs, supply voltage, air flow and the type of board (multi-layer).

#### Table 6. Thermal Resistance  $\theta_{JA}$  for 8 Lead TSSOP, Forced Convection

![](_page_10_Picture_161.jpeg)

#### **3. Calculations and Equations.**

The purpose of this section is to derive the power dissipated into the load.

LVPECL output driver circuit and termination are shown in *Figure 6.*

![](_page_11_Figure_4.jpeg)

**Figure 6. LVPECL Driver Circuit and Termination**

To calculate worst case power dissipation into the load, use the following equations which assume a 50 $\Omega$  load, and a termination voltage of  $V_{CC}$  – 2V.

- $\bullet$  For logic high,  $\mathsf{V}_{\mathsf{OUT}}$  =  $\mathsf{V}_{\mathsf{OH\_MAX}}$  =  $\mathsf{V}_{\mathsf{CC\_MAX}}$   $-$  0.9V  $(V_{\text{CC\_MAX}} - V_{\text{OH}\_\text{MAX}}) = 0.9V$
- $\bullet$  For logic low,  $\mathsf{V}_{\mathsf{OUT}}$  =  $\mathsf{V}_{\mathsf{OL\_MAX}}$  =  $\mathsf{V}_{\mathsf{CC\_MAX}}$   $-$  **1.7V** (VCC\_MAX – VOL\_MAX) = **1.7V**

Pd\_H is power dissipation when the output drives high.

Pd\_L is the power dissipation when the output drives low.

Pd\_H = [(V<sub>OH\_MAX</sub> – (V<sub>CC\_MAX</sub> – 2V))/R<sub>L</sub>] \* (V<sub>CC\_MAX</sub> – V<sub>OH\_MAX</sub>) = [(2V – (V<sub>CC\_MAX</sub> – V<sub>OH\_MAX</sub>))/R<sub>L</sub>] \* (V<sub>CC\_MAX</sub> – V<sub>OH\_MAX</sub>) =  $[(2V - 0.9V)/50\Omega] * 0.9V = 19.8$ mW

Pd\_L = [(V<sub>OL\_MAX</sub> – (V<sub>CC\_MAX</sub> – 2V))/R<sub>L</sub>] \* (V<sub>CC\_MAX</sub> – V<sub>OL\_MAX</sub>) = [(2V – (V<sub>CC\_MAX</sub> – V<sub>OL\_MAX</sub>))/R<sub>L]</sub> \* (V<sub>CC\_MAX</sub> – V<sub>OL\_MAX</sub>) =  $[(2V – 1.7V)/50 $\Omega$ ] * 1.7V = 10.2mW$ 

Total Power Dissipation per output pair = Pd\_H + Pd\_L = **30mW**

# **Reliability Information**

#### Table 7.  $\theta_{JA}$  vs. Air Flow Table for a 8 Lead TSSOP

![](_page_12_Picture_146.jpeg)

### **Transistor Count**

The transistor count for 843251-04 is: 1891

# **Package Outline and Package Dimensions**

![](_page_12_Figure_7.jpeg)

![](_page_12_Figure_8.jpeg)

![](_page_12_Picture_147.jpeg)

Reference Document: JEDEC Publication 95, MO-153

# **Ordering Information**

## **Table 9. Ordering Information**

![](_page_13_Picture_35.jpeg)

# **Revision History Sheet**

![](_page_14_Picture_77.jpeg)

![](_page_15_Picture_0.jpeg)

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